

isc Silicon NPN Power Transistor

BUV62A

DESCRIPTION

- With TO-3 packaging
- Large collector current
- Low collector saturation voltage
- High power dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

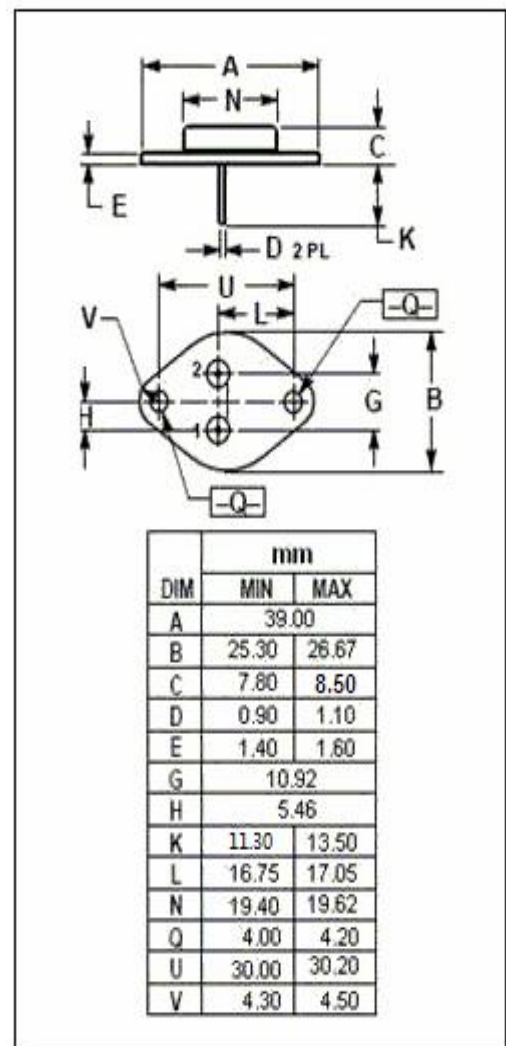
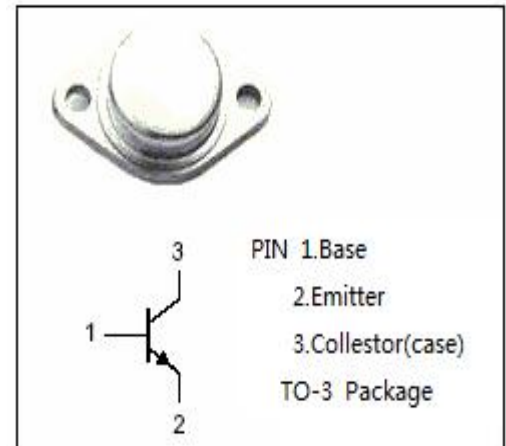
- Designed for use in DC-DC converter
- Driver of solenoid or motor
- For audio amplifier applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	400	V
V _{CEO}	Collector-Emitter Voltage	300	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current-Continuous	40	A
I _{CM}	Peak Collector Current	60	A
I _B	Base Current	8	A
P _C	Collector Power Dissipation@T _C =75°C	250	W
T _J	Junction Temperature	-55~200	°C
T _{stg}	Storage Temperature	-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.7	°C/W



isc Silicon NPN Power Transistors**BUV62A****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	300		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=50\text{mA}; I_E=0$	400		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}; I_C=0$	7		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=15\text{A}; I_B=1.5\text{A}$		0.9	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=15\text{A}; I_B=1.5\text{A}$		1.3	V
I_{CEO}	Collector Cutoff Current	$V_{CE}=300\text{V}; I_B=0$		1.0	mA
I_{CBO}	Collector Cutoff Current	$V_{CB}=400\text{V}; I_E=0$		1.0	mA
h_{FE}	DC Current Gain	$I_C=5\text{A}; V_{CE}=4\text{V}$	40	50	